
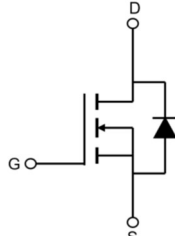


Description

Features <ul style="list-style-type: none"> ● 30V, 50A ● $R_{DS(ON)} < 7.5m\Omega$ @ $V_{GS} = 10V$ ● $R_{DS(ON)} < 14m\Omega$ @ $V_{GS} = 4.5V$ ● Advanced Trench Technology ● Provide Excellent $R_{DS(ON)}$ and Low Gate Charge ● Lead free product is acquired 	Application <ul style="list-style-type: none"> ● Load Switch ● PWM Application ● Power management <p>100% UIS 100% ΔV_d</p>
 <p>TO-252</p>	 <p>Schematic Diagram</p>

Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
VSM50N03-T2	VSM50N03	TAPING	TO-252	13inch	2500	25000

Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Symbol	Parameter	Max.	Units
V _{DSS}	Drain-Source Voltage	30	V
V _{GSS}	Gate-Source Voltage	±20	V
I _D	Continuous Drain Current	T _C = 25°C T _C = 100°C	50 33 A A
I _{DM}	Pulsed Drain Current ^{note1}	200	A
E _{AS}	Single Pulsed Avalanche Energy ^{note2}	36	mJ
P _D	Power Dissipation	T _C = 25°C	33 W
R _{θJC}	Thermal Resistance, Junction to Case	3.8	°C/W
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +175	°C

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance <small>note3</small>	V _{GS} =10V, I _D =25A	-	5.8	7.5	mΩ
		V _{GS} =4.5V, I _D =15A	-	10	14	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1.0MHz	-	1140	-	pF
C _{oss}	Output Capacitance		-	175	-	pF
C _{rss}	Reverse Transfer Capacitance		-	151	-	pF
Q _g	Total Gate Charge	V _{DS} =15V, I _D =25A, V _{GS} =10V	-	13.3	-	nC
Q _{gs}	Gate-Source Charge		-	3.1	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	5	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =15V, I _D =25A, R _{GEN} =3Ω, V _{GS} =10V	-	15	-	ns
t _r	Turn-on Rise Time		-	19	-	ns
t _{d(off)}	Turn-off Delay Time		-	35	-	ns
t _f	Turn-off Fall Time		-	21	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	50	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	200	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =30A	-	-	1.2	V
t _{rr}	Body Diode Reverse Recovery Time	I _F =30A, dI/dt=100A/μs	-	25	-	ns
Q _{rr}	Body Diode Reverse Recovery Charge		-	26	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: $T_J=25^{\circ}\text{C}$, $V_{DD}=15V$, $V_G=10V$, $R_G=25\Omega$, $L=0.5mH$, $I_{AS}=12A$

3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

Typical Performance Characteristics

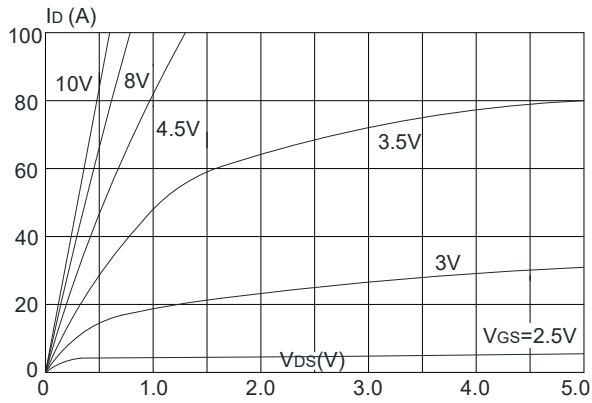
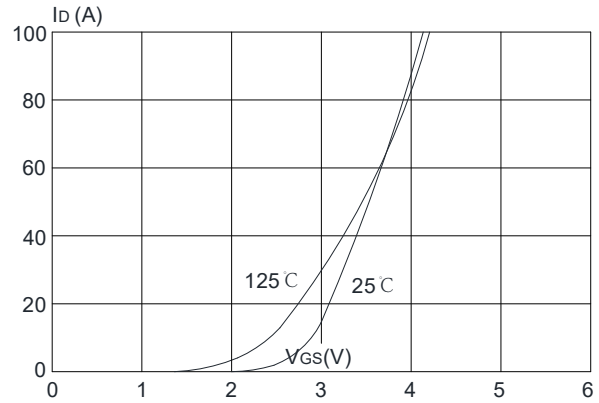
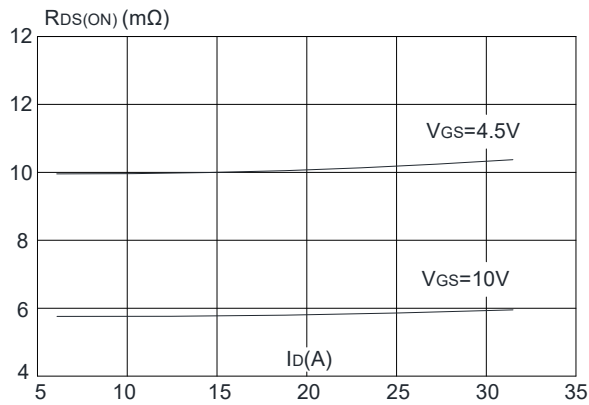
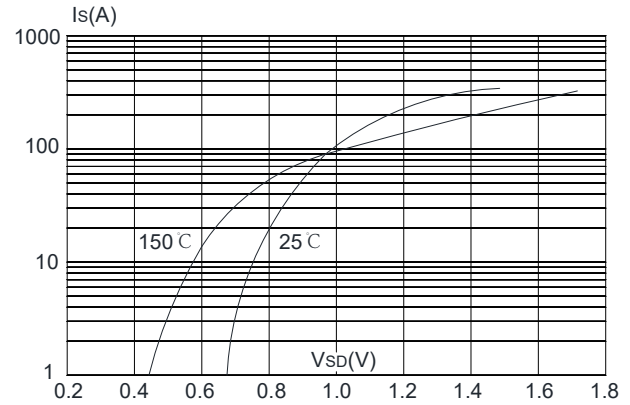
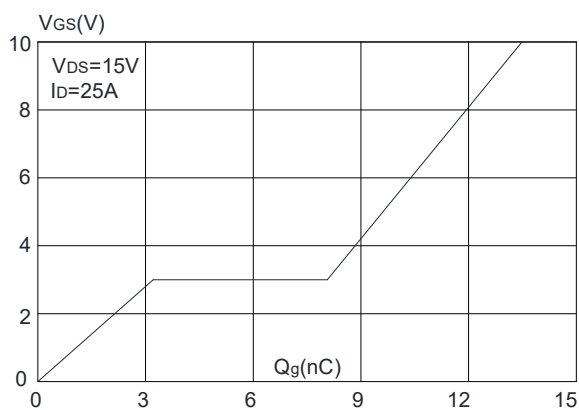
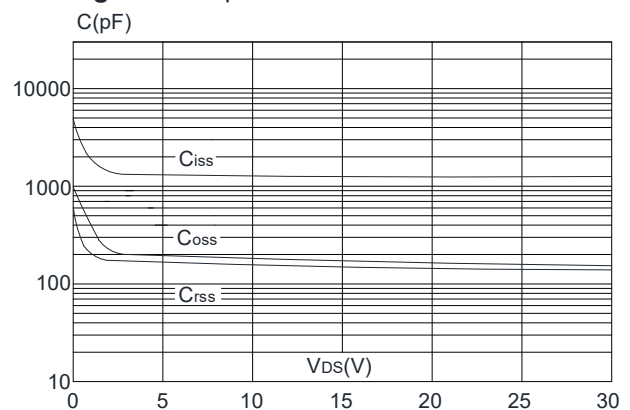
Figure1: Output Characteristics

Figure 2: Typical Transfer Characteristics

Figure 3: On-resistance vs. Drain Current

Figure 4: Body Diode Characteristics

Figure 5: Gate Charge Characteristics

Figure 6: Capacitance Characteristics


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

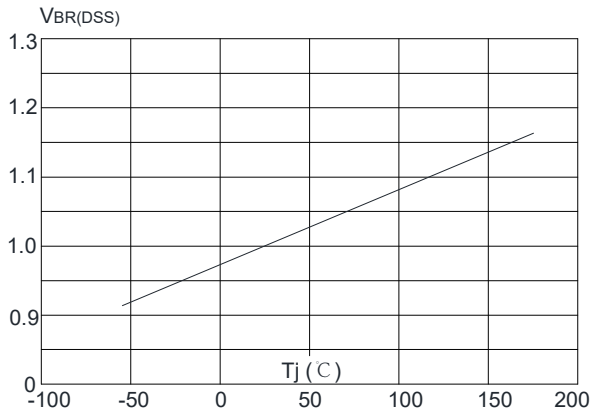


Figure 8: Normalized on Resistance vs. Junction Temperature

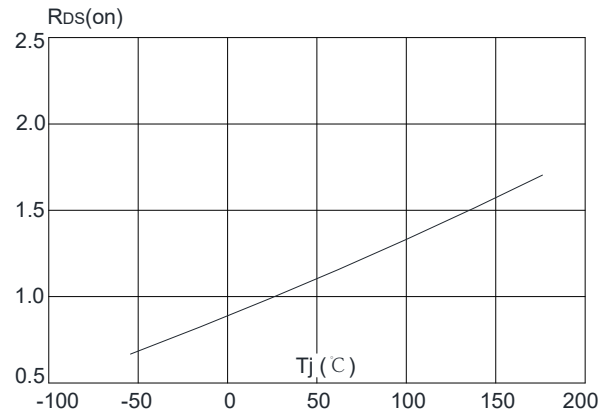


Figure 9: Maximum Safe Operating Area

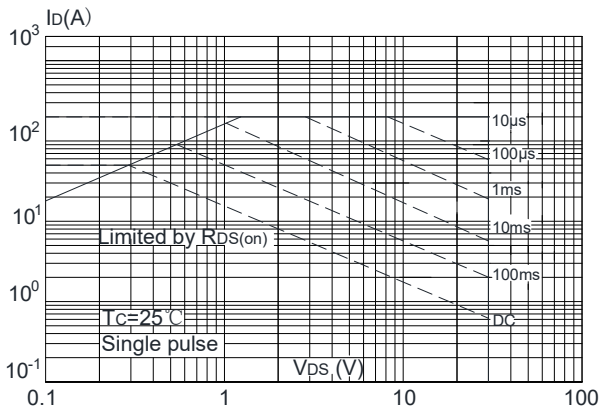


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

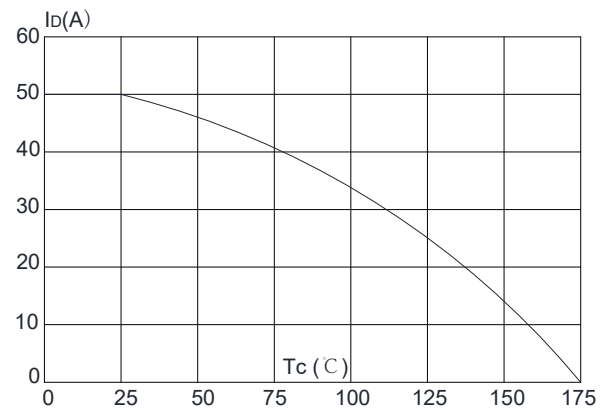
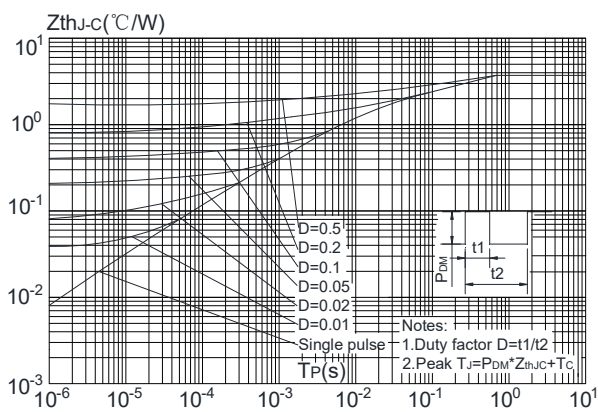


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



Test Circuit

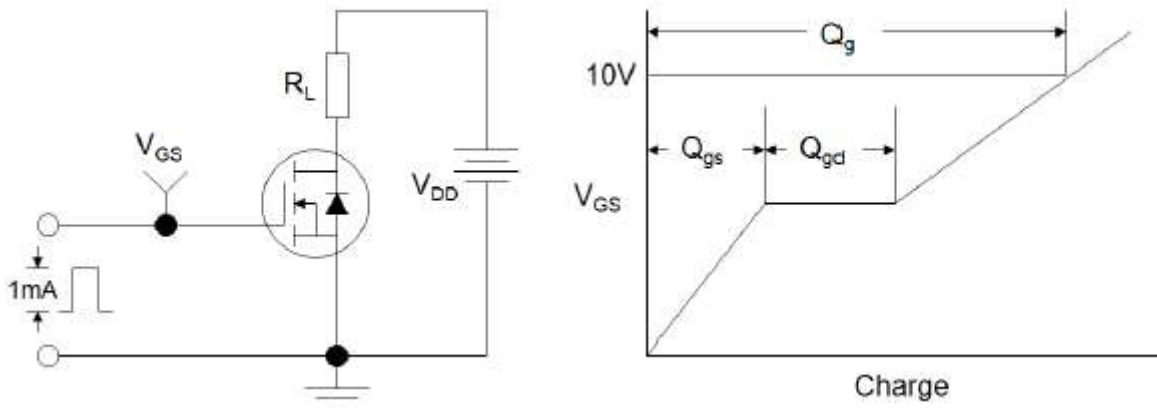


Figure1:Gate Charge Test Circuit & Waveform

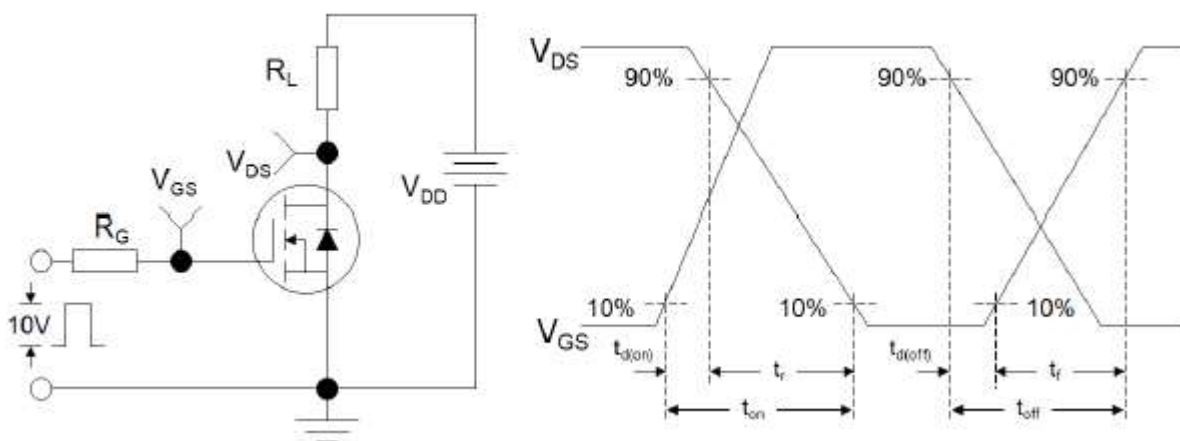


Figure 2: Resistive Switching Test Circuit & Waveforms

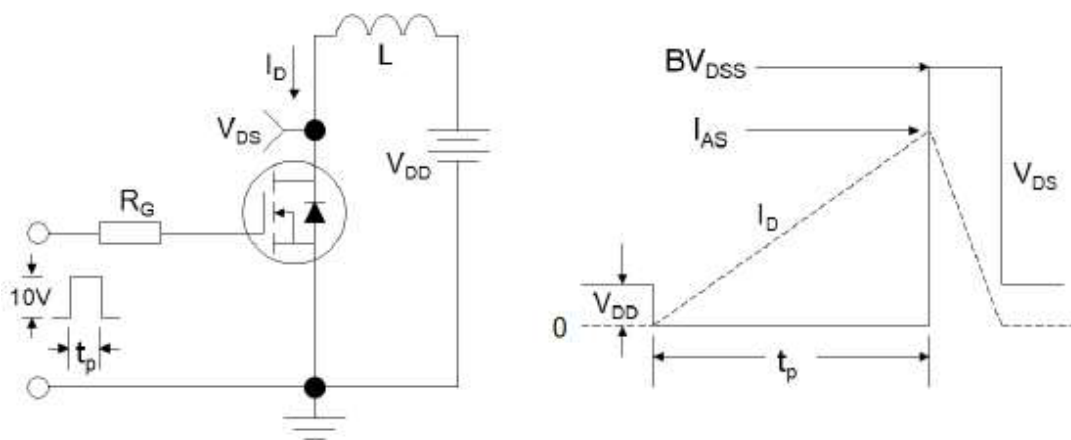


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms